



1SS352

1SS352 Silicon Epitaxial Planar Switching Diode

Features

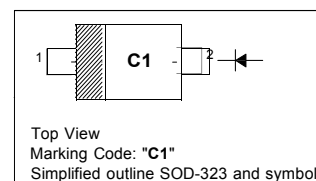
- Low forward voltage
- Fast Reverse Recovery Time
- Small TotalCapacitance

Application

- Ultra high speed switching

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

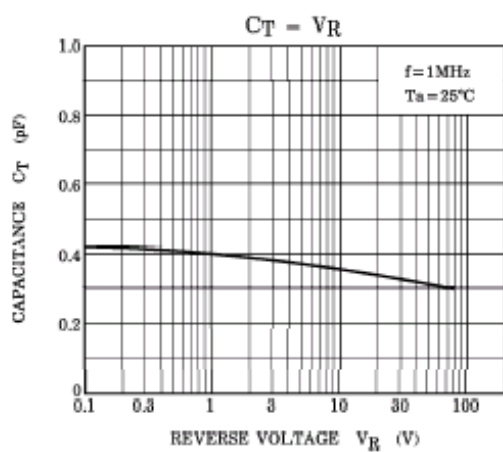
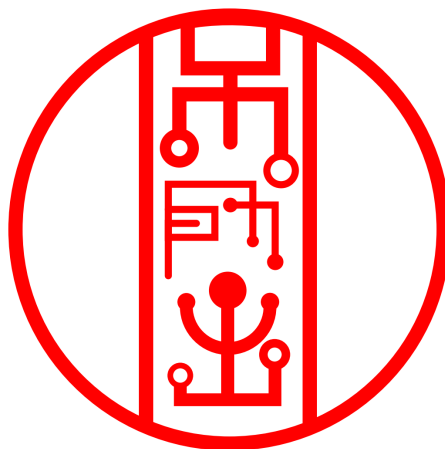


Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Maximum (Peak) Reverse Voltage	V_{RM}	85	V
Reverse Voltage	V_R	80	V
Average Rectified Forward Current	$I_{F(AV)}$	100	mA
Maximum (Peak) Forward Current	I_{FM}	200	mA
Surge Forward Current (10 ms)	I_{FSM}	1	A
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$	V_F	1.2	V
Reverse Current at $V_R = 30\text{ V}$ at $V_R = 80\text{ V}$	I_R	0.1 0.5	μA
Total Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_T	3	pF
Reverse Recovery Time at $I_F = 10\text{ mA}$ to $I_R = 1\text{ mA}$, $V_R = 6\text{ V}$, $R_L = 100\ \Omega$	t_{rr}	4	ns





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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323

